

~~TKESHEIASHVILI~~ ~~L. K.~~
KOMETIANI, P. A., TKESHEIASHVILI, L. K., and OVSYANKO, T. A.

"Applications of Phosphorous Esters of Choline, Ethanolamine and Serine to
Phospholipides Synthesis in Brain,"

paper to be presented at 2nd UN Intl. Conf. on the peaceful uses of Atomic
Energy, Geneva, 1 - 13 Sept 58.

TKESHELASHVILI, L. M., Cand Med Sci -- (diss) ■ "Treatment of diaphysial
fractures of both bones of the forearm by intra-osseous fixation."
Tbilisi, 1958. 25 pp (Tbilisi [†]_A State Med Inst), 200 copies (KL, 15-58,
#14 119)

-86-

21(4); 27(0)
 International Conference on the Peaceful Uses of Atomic Energy. 2d, Geneva, 1958
 (Biology, agriculture, medicine; radiobiology, radiotronics, and Radiation Medicine)
 Moscow, Tad-no Glav. prep. no ispol'zovaniyu atomnoy energii pri
 trudyu. Mezhdunarodnyy SSSR. 1959. 429 p. 6,000 copies printed. (Series:
 General Eds.: A.V. Lebedinsky, Corresponding Member, USSR Academy of Medical
 Sciences; Ed.: Z.S. Shirokova, Tech. Ed.: T.S. Masal'.
 PURPOSE: This book is intended for physicians, scientists, and engineers
 radiation medicine are taught.

CONTENTS: This is Volume 5 of a 6-volumes set of reports delivered by Soviet
 scientists at the Second International Conference on the Peaceful Uses of Atomic
 Energy, held on September 1-13, 1958 in Geneva. Volume 5 contains
 32 reports edited by Candidates of Medical Sciences S.V. Lebedinsky and V.V.
 Slobodcikov. The reports cover problems of Medical Sciences. S.V. Lebedinsky and V.V.
 Slobodcikov. The reports cover problems of the biological effects of ionizing
 radiation, future consequences of radiation in medical and biological research,
 in medical and biological research, uses of atomic energy for diagnostic
 and therapeutic purposes, soil absorption of atomic energy for diagnostic
 their intake by plants, and their storage in plants and food products.
 References accompany each report.

Reports of Soviet Scientists (Cont.)

Medvedev, E.M., N.I. Shul'zhenko, and I.M. Shul'zhenko. Some Results of Labeling
 Cells with ³⁵ Sulfur in Biological Studies (Report No. 2070) 212
 Slobodcikov, S.M. Special Features of Allium Synthesis in the Plant and Animal
 Kingdom (Report No. 2248) 212
 Lebedinsky, S.V. Control Mechanism of the Thyroid Gland Functions by the
 Central Nervous System (Report No. 2222) 227
 Poliak, S.M. Effect of Various Factors on the Biochemistry of Thyroxine Pro-
 duced by the Thyroid Gland (Report No. 2077) 239
 Dement'ev, P.A., L.I. Tashkhanova, and T.I.B. Chernyak. Using Phosphorus
 Isotopes for Studies in Biochemistry. Part I. ³²P-Phosphorus in Phospholipid Synthesis in the
 Nerve (Report No. 2019) 251
 Puchkov, D.L. Using ³⁴S and ³⁵S to Study Metabolism in Muscles (Report No.
 2239) 263
 Puchkov, D.L. Relative Characteristic Rate of the Three Fissionable Compounds,
²³⁵U, ²³⁸U, and ²³⁹Pu, in the Organism (Report No. 2076) 273
 Poliak, S.M. Using Radioactive Isotopes in the Clinic for Diagnostic and
 Therapeutic Purposes (Report No. 2066) 281
 Gulyaev, V.M., E.P. Radovitskaya, and S.P. Rabinovitz. Isotopic Radiography and
 Electronmicroscopy for the Localization of Radioisotopes (Report No. 2069) 297
 Gulyaev, V.M. and G.M. Drash. Study of the Free Translabelation of Substances
 in the Organism by Means of Gamma Emitting Isotopes (Report No. 2061) 307
 Gulyaev, V.M., N.I. Tikhonova, T.O. Pereshina, V.M. Tikhonov, V.D. Kharlamov,
 S.V. Slobodcikov, T.S. Shirokova, O.I. Chubrikov, A.P. Sogol'shcheva, and T.S.
 Slobodcikova. Methods of Using Isotopic Isotopes in the Production of Bacterial
 Preparations (Report No. 2072) 311
 Chelochkin, V.M., L.M. Slobodcikova, and G.E. Fele'shcheva. Description of
 Microorganisms of Strontium and Calcium in Soils (Report No. 2310) 329
 Gulyaev, V.M., L.M. Slobodcikova, and G.E. Fele'shcheva. Description of
 Microorganisms of Strontium and Calcium in Soils (Report No. 2310) 346

KOMETIANI, P.A.; TKESHELASHVILI, L.K.

Conversions of phosphoric esters of choline, ethanolamine, and
serine in the brain. Ukr.biokhim.zhur. 31 no.6:913-936 '59.

(CHOLINE)

(ETHANOL)

(SERINE)

(MIRA 13:5)

TKESHELASHVILI, L.K. (Tbilisi)

Changes in the mucous membrane of the pharynx during the menstrual cycle. Zhur. ush., nos. i gorl. bol. 23 no.4: 63-65 Jl-Ag'63. (MIRA 16:10)

1. Iz kliniki bolezney ukha, gorla i nosa (zav. - prof. S.N. Khechinashvili) Tbilisskogo instituta usovershenstvovaniya vrachey i iz Nauchno-issledovatel'skogo instituta fiziologii i patologii zhenshchiny (zav. - prof. I.F. Zhordania [deceased]) Ministerstva zdravookhraneniya Gruzinskoy SSR.
(MENSTRUATION) (PHARYNX)

KIPSHIDZE, N. N.; CHUMBURIDZE, T. I.; TKESHELASHVILI, L.K.; TVIDDIANI, D.D.;
TORDIYA, M. V.; DUMBADZE, Z. G.; SALUKVADZE, N. S.; DIDERASHVILI, A. A.;
GAVAKHISHVILI, N. N.

Studies on Cardiovascular System, some Biochemical, Hematologic and
Haemostatic Blood Indications in Old Age. Clinical Cardiology

Gerontology, 6th International Congress, Copenhagen, Denmark
11-16 August 1963

TKESHELASHVILI, L.K.; KOMETIANI, P.A.

Studying biochemical transformations of phosphoryl serine in the
brain. Trudy Inst. fiziol. AN Gruz. SSR 12:163-173 '61.
(MIRA 15:2)
(BRAIN) (SERINE)

TKESHELASHVILI, L.M.; SIMONISHVILI, A.Sh.

Internal fixation ~~in fractures~~ during childhood. Soob. AN
Gruz. SSR 25 no. 3:357-362 S '60. (MIRA 14:1)

1. Tbilisskiy gosudarstvennyy institut usovershenstvovaniya
vrachey. Predstavлено akademikom K.D. Eristavi.
(INTERNAL FIXATION IN FRACTURES)

TKESHELASHVILI, L.M.

Intraosseous fixation in tubular bone fractures with a pin
made from a cow's horn. Trudy Tbil. GIDUV 6:397-405 '62.
(MIRA 16:2)
(INTERNAL FIXATION IN FRACTURES)

TKESHELASHVILI, N.K., kand.tekhn.nauk; ASHCHIAN, O.A., kand.tekhn.nauk;
OSTASHVILI, T.I.

Mechanical injuries to tea leaves and investigating their
effect on the quality of production for the purpose of im-
proving designs of plucking machinery. Trudy VNIICHP no.1:71-82
'58. (MIRA 12:5)

(Tea machinery)

NOGAYDELI, A.I.; TKESHELASHVILI, R.Sh.; NAKAIDZE, L.I.

Reaction of dimethyldichlorosilane with 1,4-dihydro-1,
4-dilithium- β -methylnaphthalene. Soob. AN Gruz, SSR
38 no. 3:559-566 Je '65. (MIRA 18:12)

1. Tbilisskiy gosudarstvennyy universitet. Submitted Jan. 30,
1965.

L 1128-66 EWT(m)/EPF(c)/EWP(j) RPL WW/RM

ACCESSION NR: AP5022931

UR/0062/65/000/008/1396/1402

546.287

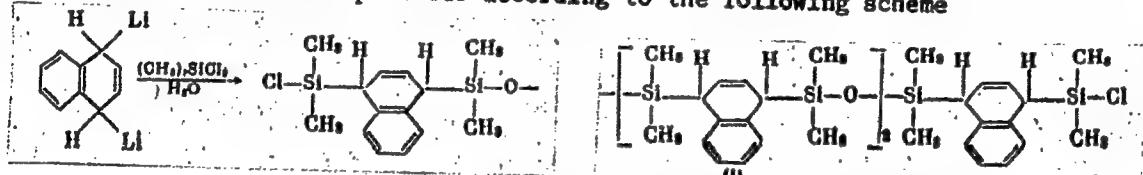
AUTHOR: Tkeshelashvili, R. Sh.; Andrianov, K. A.; Nogaydeli, A. I.

TITLE: Reaction of dimethyl- and phenylmethyldichlorosilanes with 1,4-dilithium-1,4-dihydronaphthalene

SOURCE: AN SSSR. Izvestiya. Seriya khimicheskaya, no. 8, 1965, 1396-1402

TOPIC TAGS: dimethyldichlorosilane, condensation reaction

ABSTRACT: The reaction of dimethyl- and phenylmethyldichlorosilanes with dilithium derivatives of naphthalene was studied to determine its usefulness in the synthesis of oligomers. The condensation reaction of 1,4-dilithium-1,4-dihydronaphthalene with dimethyldichlorosilane proceeds according to the following scheme

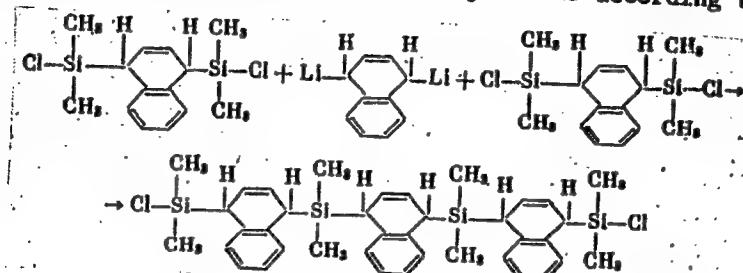


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ACCESSION NR: AP5022931

The reaction product is a tetramer with a boiling temperature of 218-220°C (at 1 mm Hg). In the absence of moisture this reaction proceeds according to



This scheme was followed also in the case of condensation with phenylmethyldichlorosilane. In this case the products were: a dimer boiling at 200-205°C (1 mm Hg) and a tetramer boiling at 245-250°C (1 mm Hg). Boiling temperatures at reduced pressure, refractive indices, and molecular weights (elemental analysis) were determined for all reaction products. In order to confirm the structure, the reaction products were hydrolyzed to the corresponding dihydroxy-derivatives with various degrees of

Card 2/3

L 1128-66

ACCESSION NR: AP5022931

polymerization and transformed into other derivatives. Orig. art. has: 2 tables. 3

ASSOCIATION: Institut elementoorganicheskikh soyedineniy Akademii nauk SSSR
(Institute of Elemental Organic Compounds, Academy of Sciences, SSSR) ^{44,55}

SUBMITTED: 09Jul64

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SUB CODE: GC, OC

NO REF Sov: 001

OTHER: 000

Card 3/3 (6)

NOGAIDELI, A.I.; TKESHELASHVILI, R.Sh.

Condensation of acetylene with acetone in the vapor phase in the presence
of caustic soda deposited on activated gumbrin. Zhur. prikl. khim. 38
no.7:1639-1640 Jl '65. (MIRA 18:7)

1. Tbilisskiy gosudarstvennyy universitet.

TKESHELASHVILI, T.V.

Hematological modifications following a major resection of the small intestine. Seob. AN Gruz. SSR 17 no. 4: 343-350 '56. (MIRA 9:9)

1. Akademiya nauk Gruzinskey SSR, Institut eksperimental'noy i klinicheskoy khirurgii i genetologii, Tbilisi. Predstavlene akademikom K.D.Kristavi.
(INTESTINES--SURGERY) (BLOOD--ANALYSIS AND CHEMISTRY)

~~TKESHELASHVILI, T.V.~~
TKESHELASHVILI, T.V.

Functional associations between segments of the small intestine.
Soob. AM Gruz.SSR 16 no.4:325-330 '55. (MLRA 8:12)

1. Akademiya nauk Gruzinskoy SSR, Institut eksperimental'noy i klinicheskoy khirurgii i gematologii Tbilisi. Predstavлено dey-stvitel'nym chlenom Akademii K.D Eristavi.
(Intestines)

TKESHELASHVILI, T.V.

Nerve regulation of the motor function of the small intestine.
Soob.AN Gruz.SSR 17 no.2:163-168 '56. (MLRA 9:8)

1. Akademiya nauk Gruzinskoy SSR, Institut eksperimental'noy i
klinicheskoy khirurgii i gematologii, Tbilisi. Predstavлено
deystvitel'nym chlenom Akademii K.D. Eristaiai.
(INTESTINES)

TKESHELASHVILI, T.V.

USSR/Human and Animal Morphology - Blood. General Problems.

Abs Jour : Referat Zhur - Biologii, No 16, 1957, 70558 R-4

Author : Tkeshelashvili, T.V.

Title : Changes In the Blood After Extensive Resection of the
Small Intestine

Orig Pub : Soobshch. AN GruzSSR, 1956, 17, No 4, 343-350

Abstract : In dogs after resection of 35-60% of the total length
of the small intestine the blood picture changed re-
latively little. The qu. of chlorides and N was in
the limits of lower and higher normals.

Card 1/1

- 102 -

TKESHELASHVILI, V.G.

Hydrobiological regimen of Lake Dzhandar. Soob. AN Gruz.
SSR 31 no. 3:675-682 S '63. (MIRA 17:7)

TKHACUSHEV, N. A.

21903. TKHACUSHEV, N. A.

Cherkesskiy sort yabloni aguyemiy. Trudy Krasnodarsk. in-ta pishch. prom-sti,
vyp. 7, 1949, s. 37-42. - Bibliogr: 8 nazv.

SO: Letopis' zhurnal'nykh Stateyj, No. 29, Moskva, 1949.

TKHACUSHEV, N. A.

21902. TKHACUSHEV, N. A.

Pomologicheskaya i khozyaystvennaya kharakteristika cherkesskogo sorta
slivy Khatsepke. Trudy krasnodarsk. in-ta iishch. prom-sti, Vyp. 7, 1949, s.

SO: Letopis' Zhurnal'nykh Statey, No. 29, Moskva, 1949.

TRIAKOVICH, N. A.

33343. Osnovnyye Cherkesskiye Sorta Grush. Sad I Ogorod, 1949, No. 10, C. 16-30

SO: Leto is' Zhurnal'nykh Statey Vol. 45, Moskva, 1949

TYHAGUSHEV, Nukha Akhmedovich

(Kuban' Agricultural Inst) - Academic degree of Doctor of Agricultural Sciences, based on his defense, 4 May 1955, in the Council of the All-Union Sci Res Inst of Plant Cultivation, of his dissertation entitled: "Adygay (Cherkassian) Gardens."

Academic degree and/or title: Doctor of Sciences

SO: Decisions of VAK, List no. 27, 24 Dec 55, Byulletin' NVO SSSR
Uncl. JFRS/NY 545

TKHAGUSHEV, N. A.

"Adygeg (Circassian) Orchards." All-Union Order of
Lenin Academy of Agriculture imeni V. I. Lenin, All-Union Inst of
Plant Breeding, Krasnodar, 1955. (Dissertation for the Degree of
Doctor in Agricultural Sciences)

SO: M-955, 16 Feb 56

1. TKHAGUSHEV, N. A.

2. USSR (600)

4. Nuts

7. Widespread introduction of nut growing. Sad i og. no.10, 1952

9. Monthly List of Russian Accessions, Library of Congress, January 1953, Unclassified.

TKHAKAKOV, U.U.

"The Protein Need of Highly-productive Cows";

dissertation for the degree of Candidate of Agricultural Sciences
(awarded by the Timiryazev Agricultural Academy, 1962)

(Izvestiya Timiryazevskoy Sel'skokhozyaistvennoy Akademii, Moscow, No. 2,
1963, pp. 232-236)

POPOV, I.S., akademik; SKOROBAGATYKH, N.N., kand. sel'skokhoz. nauk;
TKHAKAKHOV, Kh.Kh., kand. sel'skokhoz. nauk; DAVYDOVA, L.P.,
kand. sel'skokhoz. nauk; FESYUN, G.I., aspirant

Protein requirements of high-yielding cows. Izv. TSKHA no.6:
191-202 '63. (MIRA 17:8)

1. Vsesoyuznaya akademiya sel'skokhozyaystvennykh nauk imeni
Lenina (for Popov).

Protein requirements of high-yielding dairy cows. *Trans. 12th N. Amer. Vet. Conf.* 164.

1. Kafedra kormleniya sel'skokhozyaistvennykh zhivotnykh (lesovodstvo), ordene Lenina sel'skokhozyaistvennoy akademii Rossiiskoi Akademii Nauk V. I. Linnikova, 2. Vsesoyuznaya obshchina nels'kohozyaistvennykh nauk Rossiiskoi V. I. Linnikova (farmerov).

1. Starshiy inzhener Tekhnicheskogo upravleniya Ministerstva

svyazi SSSR (for Bogorodskiy) 2. Nachal'nik laboratorii Nauchno-

issledovatel'skogo instituta Ministerstva radiotekhnicheskoy

promyshlennosti (for Tikhonov).

((Phototelegraphy))

The type FTA-M facsimile transmitter. Vest. sviazi 17 no.2:3-5
F '57. (MLRA 10:3)

"TKh. 85/11/14

UDAYUISHKO, A., podpolkovnik; GUIN, V., ryten .; KALIBAY V, A. bardit
podpolkovnik

Important problem. Voen.vest. Russ. SSSR. 1970. (RUSSIA)
(Russia--Army--1970--Officers)

KUSHKHOV, Anatoliy Khazhbiyevich; TKHASHOKOV, A.P. et al.

[Outline of the history of botanical study of the
Kabardino-Balkar A.S.S.R.] Csherk istorii botaničes-
skogo izucheniia Kabardino-Balkarii. Mel'chik, Kuban'-
Balkarskoe knizhnoe izd-vo, 1962. 145 p. (MKA i8:3)

TKHAKULOV, N.I.

SHAUTSUKOVA, L.K., starshiy prepodavatel'; TKHASHOKOV, N.I., student;
KHAPAZHEV, T.Sh., student; KHAKULOV, L.A., student; DZOBLAYEV, A.A.,
student.

Physiological and biochemical change during amytal-induced sleep in
rabbits. Uch.zap.Kab.gos.ped.inst. no.10:113-127 '56. (MLRA 10:3)
(SLEEP-THERAPEUTIC USE) ('AMATYL')

TKHASHONOV, A. I.

USSR/Pharmacology, Toxicology - Narcotics.

U-1

Abs Jour : Ref Zhur - Biol., No 3, 1958, 12845

Author : Shautsukova, L.K., Tkhashonov, N.I., Khapazhev, T.Sl.,
Khakulov, L.A., Dzoblayev, A.A.

Inst :

Title : Certain Physiologic and Biochemical Changes in Rabbits
During Amytal-Induced Sleep.

Orig Pub : Uch. Zap. Kabardinsk. gos. ped. in-t, 1956, vyp. 10, 113-
126.

Abstract : Experiments were performed on male rabbits. A 15% solution of sodium amytal in a dose of 1.5-2 ml. was administered into the ear vein on 3 successive days. During the amytal-induced sleep, total plasma proteins decreased in proportion to the duration of the sleep. Blood sugar and iron decreased during the first two days but then began to increase until the sleep was terminated. During the amytal-induced sleep there was a decrease in Hb. and

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IKHEDZE, L.M.

PAGE: 100 WORK EXPERTISE 507/27/53
International Conference on the Peaceful Uses of Atomic Energy. Genva, 1958.

Doklady sverkachikh uchenykh: Polnichene i priblizhennye litsopry (Report of Soviet Scientists. Production and Application of Isotopes) Moscow: Atomizdat, 1959. 580 p. (series: ESS: Trade, vol. 6) 8,000 copies printed.

Eds. (Title page): G.V. Arshavsky, Academician and I.I. Sverdlov, Corresponding Member, USSR Academy of Sciences; Ed. (inside back): Z.D. Andronov. Tech. Ed.: Z.D. Andronov.

PURPOSE: This book is intended for scientists, engineers, physicians, and biologists engaged in the production and application of atomic energy to peaceful uses; for professors and graduate and undergraduate students of higher technical schools where nuclear science is taught; and for the general public interested in atomic science and technology.

CONTENTS: This is volume 6 of a 6-volume set of reports delivered by Soviet scientists at the Second International Conference on the Peaceful Uses of Atomic Energy held in Geneva from September 1 to 12, 1958. Volume 6 contains 52 reports on: 1) modern methods for the production of stable radioactive isotopes and their labelled compounds; 2) research results obtained with the aid of isotopes in the field of chemistry, metallurgy, machine building, and agriculture; and 3) dosimetry of isotopic radiation. Volume 6 was edited by S.V. Izravsky, Candidate of Technical Sciences; V.S. Frashov, Candidate of Chemical Sciences; and V.V. Sedyay, Candidate of Medical Sciences. See Sov/2081 for titles of volumes 1-5. References appear at the end of the articles.

20. Chardin, V.A. S.A. Ilnitsky and N.V. Shcherbina-Slobodskaya. Radioactive isotopes for solving problems in epidemiology (Report No. 2327) 375

20. Arshavsky, G.V. Radioisotopic Phenomena in the Living Organism (Report No. 2200) 347

20. Sverdlov, I.I. (Deceased). Soiuz. Trudov. Perekrestok of the Sixth. The Division in the albums of the book, and The Secretions From the Organism of the Human (Report No. 2318) 352

20. Arshavsky, G.V., I.D. Arshavskaya, V.A. Sedyay, G.A. Cherny, G.Z. Pashinian, L.M. Ikhedze, T.V. Tsvetkova, T.M. Gorbacheva, and S.D. Slobodskaya. Radiation Killing of Tumors of the Mammary Gland (Report No. 2321) 362

20. Slobodskaya, S.D. and L.V. Nekrasitsky. Studying the Effect of Isotopic Radiation on the Proteolysis of Potato Tissues With Respect to Tissue-Lysis Stages (Report No. 2331) 370

TKh. Tbilisi - 1958.
ARIFOV, U. A., BARNOV, V. A., GUMANSKIY, G. A., KLEYN, G. A., PASHINSKIY, S. Z.,
TKHELIDZE, L. M., TSWITSKHADZE, T. V., CHKHELIDZE, T. H., and SHENKOV, S. N.

"Treatment of Silkworm Cocoons by Radiation."

paper to be presented at 2nd UN Intl'. Conf. on the peaceful uses of Atomic
Energy, Geneva, 1 - 13 Sept 58.

GADAKHABADZE, V.I.; TKHELIDZE, L.M.

The introduction of white cocoon and hybrid cocoons. Tekst.
(MLRA 9:10)
prom. 16 no.8:8 Ag '56.

(Georgia--Silk manufacture)

TKHILADZE, G.

Methods for economizing drying oil. Stroitel' 2 no.6:8-9 Je '56.
(MIRA 10:1)

1. Nachal'nik TSentral'noy nauchno-issledovatel'skoy laboratori
Glavmosstroya.
(Painting, Industrial) (Emulsions)

SIZOV, Vasiliy Nikolayevich, prof., doktor tekhn.nauk;
RUDENKO-MORGUN, Ivan Yakovlevich, dots., kand. tekhn.
nauk; TAKHILADZE, Georgiy Rodionovich, inzh.; USEKO,
Vasiliy Mitrofanovich, kand. tekhn. nauk; SHVIDENKO,
V.N., prof., retsenzent; DANILEVSKIY, A.S., inzh.,
retsenzent; KUPERSHMIDT, L., red.

[Technology of construction] Tekhnologija stroitel'nogo
proizvodstva. [By V.I.Sizov i dr. Moskva, Vysshaia shkola,
1964. 613 p. (MIRA 19:1)]

TKHILADZE, G. R.; VOLGDARSKIY, G. I.

Drilling and Boring

A drill with hard-alloy tip for drilling holes in brick walls. Biul. stroi. tekhn. 9 no. 1, 1952. Minmashstroy, Trest Otdeletstroy; Inzh.

SO: Monthly List of Russian Accessions, Library of Congress, April ² 1953, Uncl.

TKHILADZE, G.R., VOLODARSKIY, G.I.

Hose Couplings

Standard hose couplings. Biul.stroi.tekh., 2, no. 14, 1952.

9. Monthly List of Russian Accessions, Library of Congress, NOVEMBER 1952 1953, Unc1.

1. TKHILADZE, G. R. ENG.
2. USSR (600)
4. Plastering
7. Rationalization of decorative work. Biul. stroi. tekhn. 9 no. 19, 1952.

9. Monthly List of Russian Accessions, Library of Congress, January 1953. Unclassified.

1. TKHILADZE, G. R.
2. USSR (600)
4. Building Machinery; Plastering
7. Mobile plastering machine units Stroi. prom. 30, no. 4, April 1952
Nachal'nik Tsentral 'noy Nauchno-Issledovatel 'skoy Stantisii Tresta,
Otdelstroy Minmashstroya.
9. Monthly List of Russian Accessions, Library of Congress, June 1952.
UNCLASSIFIED

SHEPELEV, A.M., inzhener; TKHILADZE, G.R., inzhener nauchnyy redaktor.

[Paper hanging] Oboinye raboty. Moskva, Gos. izd-vo lit-ry po
stroitel'stvu i arkhitekture, 1953. 31 p. (MLRA 7:?)
(Paper hanging) (Wallpaper)

TKHILADZE, G.R., inzhener, nachalnik.

Finishing of building facades in winter. Stroi.prom. vol. 31 no.9:17-19
(MLBA 6:9)
S '53.

1. TSentral'naya nauchno-issledovatel'skaya laboratoriya Ministerstva
stroitel'stva.
(Plastering--Cold weather conditions)

TKHILADZE G. R. AND VOLODARSKIY, G. I.

3352 TKHILADZE G. R. AND VOLODARSKIY, G. I.

Mekhanizatsiya parkegnykh rabot. M., 1954 16 S. S chert. 26 sm (Akad. Nauk SSSR. In-T Tekhn. Ekonom. informatsii. Periodich. informatsiya tema no 47)
1.000 ekz B ts Na obl ovt Ne ukazany (54-57189) 694.631 a 3.0025

TKHILADZE, G.R.

[Equipment for the mechanization of plastering] Oborudovanie
dlia mekhanizatsii stukaturnykh rabot. Moskva, Gos. izd.
lit. po stroit-vu i arkhitekture, 1954. 216 p. (MIRA 8:1D)

TKHILADZE G. A.

KRESTOV, M.A., redaktor; TKHILADZE, G.R., inzhener, nauchnyy redaktor;
BEGAK, B.A., redaktor; PERSON, M.N., tekhnicheskiy redaktor.

[Technology of finishing work] Otdelochnaya tekhnika. Pod obshchey
red. M.A.Krestova. Moskva, Gos. izd-vo lit-ry po stroitel'stvu i
arkhitekture. No. 2. 1954. 82 p. (MLRA 7:11)

1. Akademiya arkhitektury SSSR, Moscow. Laboratoriya otdelochnykh
rabot.

(Façades) (Painting, Industrial)

TKHILADZE, G.R., inzhener.

For progressive technology in painting. Gor.khoz. Mosk. 29 no.11:
27-31 N '55. (MLRA 9:3)
(Painting, Industrial)

MESHKOVSKAYA, V.V.; SMIRNOV, V.Ya.; ANTIPOV, M.M.; TKHILADZE, G.R.

Mobile mechanized machine for preparing paint components. Rats. i izebr.
predl.v strel.no.123:6-9 '55. (MIRA 9:?)
(Paint machinery)

SMIRNOV, V.Ya.; PEREPELKINA, M.S.; ANTONOV, M.M.; TKHILADZE, G.R.

Mobile all-purpose machine for parquet floor layers. Rats. i izebr.
predl.v strel. №.123:13-17 '55. (MLRA 9:7)
(Parquetry)

VASADZE, Ye.N., ~~TKHINVALELI, G.Kh.~~

Turbodrilling of mine shafts. Azerb. neft. khoz. 37 no.8:
21-24 Ag '58. (MIRA 11:11)
(Shaft sinking)

TKHIR, D.G.

Equipment and technology for drilling structural-prospecting wells on the territory of the East Ukrainian oil- and gas-bearing region. Neft. i gaz. prom. no. 4277-29 0-0 '64
(MIRA 1882)

TKHIR, D.G.

Turbodrilling in sinking structural wells. Neft. i gaz.
prom. 3:35-36 J1-S '65. (MIRA 18:11)

L 05143-57 ENT(1)/FCC GW
ACC NR: AR6017547

SOURCE CODE: UR/0169/66/000/001/D014/D014

AUTHOR: Parkhomovskiy, O.A.; Andreyeva, R.I.; Burakovskiy, L.Ye. Goncharova, T.A.; Grigor'yeva, A.I.; Ivanets, N.I.; Ivanyuta, M.M.; Kozar, L.T.; Raykher, L.D.; Senina, A.S.; Tkachenko, Zh. Ya.; Tkhir, D.G.

TITLE: Determination of the development level of the technique and technology of geological prospecting for oil and gas in the Ukraine

SOURCE: Ref. zh. Geofizika, Abs. 1D97

REF SOURCE: Tr. Ukr. n.-i. geologorazved. in-t, vyp. 10, 1965, 10-17

TOPIC TAGS: prospecting, seismic prospecting, oil prospecting, gas prospecting, PETROLEUM, magnetometer, gravimetry / M-2 MAGNETOMETER, UKRAINE

ABSTRACT: Geological-geophysical prospecting for oil and gas, completed on the Ukraine during 1960-1962 was analyzed. At present all the oil-bearing territory of the Ukraine is covered by prospecting survey with the M-2 magnetometer. The cost of study was 46.4 roubles/km². The output and precision of the aeromagnetic survey is much better. The gravimetric survey is basically complete. The cost of the total survey was 92.2 roubles per km² in 1960 and 47.2 roubles in 1962. Highly precise gravimeters (.01 - .03 mgal) can elucidate various anomalies. Inspite of the relative cheapness of the electro-recon method, and its mobility, it has not been afforded the deserved development in the Ukraine. Volume of seismic work reaches 87% of the total geophysi-

Card 1/2

UDC: 550.830(477)

L 06143-67
ACC NR: AR6017547

cal work volume. Cost of 1 km of seismic profile work was 560-850 roubles. In 1962, seismic reconstructing instrumentation for the automatic processing of seismograms and design of boring sections has been developed. Technoeconomical indices of structural mapping boring are very high; those of structural-recon boring are at relatively low levels. On the basis of consideration of the possibilities of each method, a methodology for the recon of oil and gas is proposed. Translation of abstract.

SUB CODE: 08

Card 2/2 MFE

TKhomirov, D.F.
TKHOMIROV, D.F.

~~Staff catchers must be improved. Avtom., telem. i sviaz'2 no.1:~~
~~(MIRA 11:1)~~
39 Ja '58.

1. Starshiy elektromekhanik Volkhovstroyevskoy distantsii signalizatsii i svyazi Kirovskoy dorogi.
(Railroads--Signaling)

ADAMOVICH, A.V., kand.tekhn.nauk; TKHOMIROV, Ya.V., kand.tekhn.nauk

Statistical investigation of the strength of the block carter
of a V-engine. Avt.prom. 27 no.8:8-11 Ag '61. (MIRA 14:10)

1. Nauchno-issledovatel'skiy avtomobil'nyy i avtomotornyy
institut.
(Automobiles--Engines)

LEVIN, V.I.; GOLUTVINA, M.M.; TKHOMIROVA, Ye.A.

Preparation of arsenic-74 from neutron-irradiated selenium.
Radiokhimiia 3 no.5:597-600 '61. (MIRA 14:10)
(Arsenic--Isotopes) (Selenium) (Neutrons)

BASARGIN, V.A., inzh.; GRINBERG, V.L., inzh.; TKHOR, A.P., inzh.;
ZAZIMKO, V.N., inzh.

Mechanization of duck breeding farms. Mashinostroenie no.5:
83-84 8-0 '64 (MIRA 18:2)

TKHOR, L.W.

Chemiluminescence of oleic acid. Trudy MGIP. Ltd. Biol. 21:
(MIRA 18:6)
203-205 '65.

TKHOR, L.F.; KOZLOV, Yu.P.

Effect of some antibiotics on the chemiluminescence of oleic acid. Biofizika 10 no.3:523-524. '65. (MIRA 18:11)

1. Biologo-pochvennyy fakul'tet Moskovskogo gosudarstvennogo universiteta imeni Lomonosova. Submitted July 11, 1964.

TKHOR, T.G.; PANKRATOV, M.A., prof., nauchnyy rukovoditel' raboty

Restoration of reflexes from the auricular skin of a rabbit as
related to the regeneration of nerves. Uch. zap. Ped. inst. Gerts.
239:131-137 '64. (MIRA 18:3)

BEDNYY, M.S.; TKHOR, V.G. (Dnepropetrovsk)

Oldest hospital in the Ukraine. Sov. zdrav, 21 no.2:60-63
'62. (MIRA 15:3)
(UKRAINE--HOSPITALS)

USSR/Farm Animals. Sheep and Goats.

Q

Abs Jour: Ref Zhur-Biol., No 17, 1958, 78766.

Author : Lermontov, V. S.; Tkhor, Ye. S...

Inst :

Title : On the Effectiveness of Winter Lambing of Sheep.

Orig Pub: Ovtsevodstvo, 1958, No 1, 5-6.

Abstract: In a test group (February birth), 5% of the ewes were barren, 0.5% of the lambs died; 124 lambs of 100 ewes were raised. In the control group (April birth) respectively: 15, 2.1 and 100. Difference in live weight of the lambs for 5 months in favor of the test group comprised: with young rams 2.7 kg, ewe yearlings

Card : 1/2

USSR/Farm Animals. Sheep and Goats.

Q

Abs Jour: Ref Zhur-Biol., No 17, 1958, 78766.

0.6 kg; in length of wool, respectively: 0.7
and 0.6 cm.

Card : 2/2

44

L 13064-63

BDS

ACCESSION NR: AT3003010

S/2927/62/000/000/0235/0235

52
51AUTHOR: Miselyuk, Ye. G.; Tomashevskaya, R. L.; Tkhonik, Yu. A.TITLE: Ten-element diode matrix (A brief information) [Report of the All-Union Conference on Semiconductor Devices held in Tashkent from 2 to 7 October 1961]SOURCE: Elektronno-dy*rochny*ye perekhody* v poluprovodnikakh. Tashkent, Izd-vo AN UzSSR, 1962, 235TOPIC TAGS: semiconductor matrix, diode matrix, ten-element matrixABSTRACT: Soviet-manufactured DM-10 ten-element diode matrices¹⁰ are intended for passive-storage computers. The DM-10 matrix comprises 10 diodes with a common base mounted on a 10 x 10 sq mm panel; it has the following parameters (with 20% spread): maximum forward current 0.25 amp, maximum peak current 1 amp, forward resistance at 0.6 v 2-4 ohms, peak resistance 5 ohms, maximum reverse current 6 microamp, breakdown voltage 60-80v, operating temperature range -50 +65C. Orig. art. has: 1 figure.ASSOCIATION: Akademiya nauk SSSR (Academy of Sciences SSSR); Akademiya nauk Uzbekskoy SSR (Academy of Sciences UzSSR); Tashkentskiy gosudarstvenny*y (Tashkent St. Un.)

Card 1/21

L 12815-63 EWT(1)/EWG(k)/EWP(q)/EWT(m)/BDS/T-2/EEC(b)-2/ES(t)-2
ASD/ESD-3 Pz-4/Pm-4 JD/IJP(C)
ACCESSION NR: AT3003011

S/2927/62/000/000/0236/0243

AUTHOR: Miselyuk, Ye. G.; Tomashevskaya, R. L.; Tkhorik, Yu. A.

76

TITLE: Germanium diffusion diodes for pulse circuits [Report at the All-Union Conference on Semiconductor Devices, Tashkent, 2-7 October, 1961]

SOURCE: Elektronno-dy*rochny*ye perekhody* v poluprovodnikakh. Tashkent, Izd-vo AN UzSSR, 1962, 236-243

TOPIC TAGS: germanium diode, IDG-1 diode

ABSTRACT: As a prerequisite to the development of high-power pulse-type Ge diodes, transients in Ge diffusion diodes were studied. Effects of resistivity and lifetime of materials, geometric factors, and p-n junction processing on the switching characteristics of diodes were investigated. Particularly, the effect of injection level (or forward current) and reverse voltage on the reverse-resistance recovery time, for various lifetimes and base thicknesses, were investigated. As a result, a new Ge diode, IDG-1, with these parameters was developed: peak current with a 0.5-microsec pulse and 1/2000 pulse duty factor, up to 15 amp; voltage drop at 1 amp, 0.6 - 0.8 v; forward resistance, 0.5 - 1.4 ohms; reverse current, 0.6 - 15

Card 1/2

L 12815-63

ACCESSION NR: AT3003011

microamp; breakdown voltage, 80-100 v; recovery time, 0.25 microsec or less; pulse forward resistance, 5 ohms; working temperature range, -100 +65C. The IDG-1 diode was tested in various computers and is recommended for use in switching circuits, ferrite-diode circuits, ferroelectric circuits, discriminators, registers, and other circuits involving heavy currents. The diode was set in small-lot production. Orig. art. has: 7 figures, 5 formulas, and 3 tables.

ASSOCIATION: none

SUBMITTED: 00

DATE ACQ: 15May63

ENCL: 00

SUB CODE: PH, OE

NO REF Sov: 006

OTHER: 008

Card 2/2

247700

37873
S/185/62/007/005/003/013
D407/D301AUTHOR: Tkhoryk, Yu.O.

TITLE: Emissivity of diffused p-n junctions

PERIODICAL: Ukrayins'kyy fizychnyy zhurnal, v. 7, no. 5, 1962,
476 - 481

TEXT: The distribution of carrier concentration in a diffused p-n junction is considered which has been obtained by the method of thermodiffusion. A formula for the emissivity of p-n junctions is obtained. It was shown by K.B. Tolpygo (Ref. 1: ZhTF, 27, 884, 1957) that the coefficient of injection γ is not a constant of the p-n junction (as in Shockley's theory), but depends on the structure of the junction, the properties of the contact metal-semiconductor and the magnitude of the current. The parameter β , called by Tolpygo the emissivity of the p-n junction, combines all these properties. In Ref. 1 (Op. cit.) the parameter β was calculated for linear and exponential distributions of the doping impurities and criteria for high emissivity (i.e. large values of β) were derived. Large values of β are particularly important for pulse diodes, where a low direct

Card 1/3

S/185/62/007/005/003/013

D407/D301

Emissivity of diffused p-n junctions

resistance is required; as pulse diodes are normally obtained by the diffusion method, it is important to derive analogous criteria for diffused p-n junctions. It is assumed that the p-n junction is formed by the diffusion of donors in a p-type semiconductor. Therefore the donor concentration decreases with the distance from the edge according to the law $\text{erfc}(x/2\sqrt{DT})$, where x is the distance, D - the diffusion coefficient of the donors, and t - the time of diffusive annealing. The n-layer is divided into 3 regions; the points ξ_1 and ξ_2 (which are dimensionless coordinates related to x), are chosen in such a way that the donor concentration can be approximated by a linear function or by an asymptotic formula. After calculations, one obtains the following formula for β :

$$\beta = \frac{N(0)/Q_+}{1 + A\xi_0 \frac{N(0)}{Q_+}}, \quad (15)$$

where Q_+ is the transmittance (for holes) of the contact; $N = n/p_p$ (n being the electron concentration and p_p - the equilibrium concen-

Card 2/5

S/185/62/007/005/003/013

D407/D501

Emissivity of diffused p-n junctions .

tration of holes in the base), $A = \epsilon \cdot \rho_0 / 4\pi\tau$. The accuracy of the above approximation is estimated. Thereby one obtains

$$1 \gg Q_+ \Xi_0 + A \xi_0^2 N(0). \quad (24)$$

Formulas (15) and (24) are in agreement with the corresponding formulas of Ref. 1 (Op.cit.). It is noted that the emissivity of the p-n junction (in the case of a linear impurity distribution) increases with $d\nu/d\xi$ (ν being related to the donor-concentration distribution); for a diffused p-n junction $d\nu/d\xi$ is a variable quantity. It is also noted that, other conditions being similar, the emissivity of diffused p-n junctions is higher than with a linear impurity-distribution. There are 1 figure and 5 references: 3 Soviet-bloc and 2 non-Soviet-bloc. The most important English-language publication reads as follows: J.R.A. Beale, Proc. Phys. Soc., 70, 1087, 1957.

ASSOCIATION: Instytut napivprovodnykiv AN URSR (Institute of Semiconductors of the AS UkrRSR) Kyyiv

SUBMITTED: January 24, 1962

Card 3/3

*TKHORIK, Yu. A.*S/109/62/007/006/021/024
D234/D308

9.4340

AUTHORS: Kolomiyets, B. T., Litvinova, E. M., Miselyuk, Ye. G.,
Tkhork, Yu. A. and Shilo, V. P.TITLE: Effect of fusible glass coating on the characteristics
of germanium diodesPERIODICAL: Radiotekhnika i elektronika, v. 7, no. 6, 1962,
1054-1055TEXT: Three types of glass coatings on germanium diffusion diodes
were tested: $As_2Se_3.I_{1.5}$; $As_2Se_3.Tl_2Se$; $2As_2S_3.Tl_2S$. The whole ex-
posed surface of the semiconductor, including the p-n transition,
was coated. A graph of a typical variation of V-A characteristics
after coating is given. The characteristics so obtained were prac-
tically unchanged over many days. Glass coating is found to im-
prove essentially the inverse branches of the characteristics. The
effect of all three types of glass is nearly the same. Improvement
of characteristics was also observed when the glass had been re-*✓ B*

Card 1/2

Effect of fusible ...

S/109/62/007/006/021/024
D234/D308

moved immediately after coating which disagrees with the result of other Soviet authors. There is 1 figure.

ASSOCIATION: Institut poluprovodnikov AN USSR; Fiziko-tehnicheskiy institut im. A. F. Joffe AN SSSR (Institute of Semiconductors, AS UkrSSR; Physico-Technical Institute im. A. F. Joffe, AS USSR)

SUBMITTED: February 13, 1961

Card 2/2

TKHORIK, Yu.A. [Tkhoryk, IU.O.]

Accumulation of minority current carriers in semiconductor
diodes with a narrow base. Ukr. fiz. zhur. 8 no.10:1128-
1141 0 '63. (MIRA 17:1)

1. Institut poluprovodnikov AN UkrSSR, Kiyev.

TKHORYK YU. O.

ACCESSION NR: AP4017393

8/0185/64/009/002/0139/0149

AUTHOR: Il'yenkov, A. I.; Tkhor'k, Yu. O.

TITLE: Measurement of short lifetimes of current carriers in semiconductor devices by the pulse method

SOURCE: Ukrayins'ky fizichny zhurnal, v. 9, no. 2, 1964, 139-149

TOPIC TAGS: semiconductor, semiconductor lifetime, pulse method, current carrier effective lifetime, diode, transistor

ABSTRACT: The effective lifetime τ_e of the minority carriers in the base region of a semiconductor device is the most important parameter which determines the frequency characteristics and the transient response of the device. Many methods for measuring τ_e in diodes have been proposed but the most practical and direct method is based on the investigation of the transient process which arises during diode switching. For values of $\tau_e \approx 10^{-7}$ sec, the measurements can be performed on an oscilloscope. When a p-n diode is switched from forward to reverse, the reverse current is established in two stages t_{lim} or phase of constant reverse current (when the diode resistance is small compared to the external circuit resistance) and the phase of current decay (which begins when the minority carrier concentration near the p-n junction goes to zero). The forward current pulse length t_1 , its magnitude I_f , as well as the magnitude of the reverse current

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ACCESSION NR: AP4017393

I_r which flows during t_{lim} , are related to τ_e by the formula:

$$\operatorname{erf} \sqrt{\frac{t_{lim}}{\tau_e}} = \frac{1}{B_0 + 1} \operatorname{erf} \sqrt{\frac{t_l + t_{lim}}{\tau_e}} \quad (1)$$

where $B_0 = \frac{Iv}{I}$ and $B_0 \geq 0.5$.

Equation (1) is valid when the base region is much longer than the diffusion length of the minority carriers and when the switching pulse has zero rise time. When the finite rise time in the leading edge of the switching pulse is taken into account the use of equation (1) may lead to serious errors. For a planar p-n junction diode switched by a trapezoidal pulse, when the forward and reverse resistances in the external circuit may be unequal (Fig. 1 of the Enclosure), the following formula is derived, which gives the desired minority lifetime τ in terms of measurable parameters:

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ACCESSION NR: AP4017393

$$1 = \frac{2(a+b+c)-1}{2a} \operatorname{erf} \sqrt{a+b+c} + \frac{\sqrt{a+b+c}}{a\sqrt{\pi}} e^{-(a+b+c)} + \\ + \frac{aB_0-b}{b} \left[\frac{2(b+c)-1}{2a} \operatorname{erf} \sqrt{b+c} + \frac{\sqrt{b+c}}{a\sqrt{\pi}} e^{-(b+c)} \right] - \\ - \frac{B_0}{b} \left(\frac{2c-1}{2} \operatorname{erf} \sqrt{c} + \frac{\sqrt{c}}{\sqrt{\pi}} e^{-c} \right). \quad (2)$$

where $a = \frac{t_f}{T}$, $b = \frac{t_p}{T}$, $c = \frac{t_e}{T}$, and the intervals t_f , t_p and t_e are defined in Fig. 2 of the Enclosure. Equation (2) can be simplified considerably if the constant reverse current interval, t_{\lim} , is shorter than the duration of the leading edge of the switching pulse (Fig. 2b). A general Laplace transform equation from which an expression analogous to Eq. (2) can be derived for any switching pulse shape, is also derived. The errors which can be encountered in calculation, when the finite duration of the leading edge of the trapezoidal pulse is neglected (as in Eq. 2), are summarized in Fig. 3 of the Enclosure. Some experimental data which support the conclusions reached in this paper are tabulated in the original. It is evident that for large B_0 values the values of τ_1 are too low. The

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ACCESSION NR: AP4017393

error $\frac{\gamma_e - \gamma_1}{\gamma_e}$ is systematic and ranges from 13.6-21.6% for $B_0 = 0.2$, from 7.2 to 17.7% for $B_0 = 0.459$ and from 22.2 to 42.4% for $B_0 = 1$. The accuracy in the estimate of γ_e is 6.6% and also $\gamma_2 < \gamma_e$ even though the error in γ_2 is smaller than in γ_1 . "The authors thank E. M. Ly*tvy*noviy for construction of the diodes." Orig. art. has: 3 figures, 1 table and 31 formulas.

ASSOCIATION: Insty*tut avtomaty*ky* ta elektrometriyi, SV AN SSSR, Novosibirsk (Institute of Automation and Electric Measurement); Insty*tut napivprovidny*kiv AN URSR, Kiev (Semiconductor Institute)

SUBMITTED: 05Aug63

DATE ACQ: 19Mar64

ENCL: 03

SUB CODE: PH

NO REF SOV: 014

OTHER: 004

Card

4/PY

L 20501-65 5WT(m)/EXP(b)/AP/41090881
ACCESSION #: AP4038646

S 0109/64/009/005/0876/0881

AUTHOR: Bondarenko, V. N.; Litvinova, E. M.; Snitko, O. V.; Tikhonik, Yu. A.

TITLE: Effect of some coatings and thermal treatment of the surface
combination rate of silicon and germanium.

SOURCE: Radiotekhnika i elektronika, v. 9, no. 5, 1964, 876-881

TOPIC TAGS: silicon, metal coated silicon, germanium, metal coated
germanium, surface recombination, surface recombination rate

ABSTRACT: An experimental investigation of the effects of (1) low-temperature
annealing of Si and Ge in He atmosphere and (2) the effect of a thin film of
As₂Se₃ on the surface recombination rate of Si and Ge.

(with a softening temperature of 109C) As₂Se₃ + Ti₂Se As₂Se₃
As₂Se₃ + Ti₂(85C) As₂Se₃ + Ti₂(70C)

Card 1/2

L 20501-65

ACCESSION NR: AP4038648

and $Tl_2S \cdot 2As_2S_3$. It is found that annealing of n- or p-type Ge results in an increase of σ by 2-3 times, a reduction of σ by a factor of 2-3 times. Annealing of Si results in 2-4 times lower σ , with a subsequent glass treatment σ was reduced to about 300 ohm⁻¹ cm⁻². The same value of σ was obtained by a vacuum rotating of n-Si on gold (700-1200 nm) at 300°C. The annealing time was 10-15 min. The annealing temperature was 300°C.

See also page 2 for formulas and tables.

ASSOCIATION: Institut poluprovodnikov AN SSSR (Institute of Semiconductors AN SSSR)

SUBMITTED: 22Mar63

ENCL: 00

SUB CODE: MM, SS

NO REF SOV: 006

OTHER: 004

Card 2/2

TKHOKR 7/14

L 14799-65 AFRL/ASD(a)-5/ESD(t)
ACCESSION NR: AP1044168

8 91 5 64 000 001 0151 1561

AUTHOR: Grigor'yev, Z. S. (Grigoryev, Z. S.)
TITLE: Dissipation of carriers in a p-n-p-n diode

SUMMARY: Ustavim krylovskiy model' dlya p-n-p-n dioda v 1964, 651-61

TOPIC TAGS: transient process, semiconductor - carrier storage, carrier dissipation, semiconductor diode

ABSTRACT: The processes of storage and dissipation of nonequilibrium charge carriers in a p-n-p-n diode are investigated. The model is based on the solution of the equations of carrier motion in the presence of a space charge. The model is in good agreement with the experimental data.

Card 1/2

L 14799-65
ACCESSION NR: AP4044168

diffusion, and in the second type by the drift. The author is grateful to
A. P. Klimenko for help with the experiment. Orig. art. has: 8 figures. 32

ASSOCIATION: Institut poluprovodnikov AN URSR (Institute of Semiconductors
AN URSR)

SUBMITTED: 19Jan64

ENCL: 00

SUB CODE: SS

NO REF SOV: 012

OTHER: 003

Card 2/2

GRIENIKOV, Z.S. [Hrybnykov, Z.S.]; TKHORIK, Yu.A. [Tkhoryk, IU.O.]

Transients of storage and decay of nonequilibrium carriers
in semiconductor diodes. Part 3. Symmetric thin diodes at
superhigh injection levels. Ukr. fiz. zhur. 9 no.9:943-947
S '64. (MIRA 17:11)

1. Institut poluprovodnikov AN UkrSSR, Kiyev.

GORBAN', A.P.; TKHORIK, Yu.A.

Device for measuring the capacitance of semiconductor diodes.
Avtom. i prib. no.2:57-60 Ap-Je '63. (MIRA 18:8)

1. Institut poluprovodnikov AN UkrSSR.

ZHURAVEL', F.A.; IL'YENKOV, A.Z.; TKHORIK, Yu.A.

Evaluation of the pulse characteristics of semi-conductor diodes.
Trudy Inst. avtom. i elektrometr. SO AN SSSR no.16-68-85 '65.
(MIFI A 18.8)

TKHORIK, Yu.A.

Effect of the dependence of the recombination speed in the plane
of a non rectifying contact from the injection level on the spread-
ing time. Radiotekh. i elektron. 10 no.3:574-576 Mr '65.

(MIRA 18:3)

TKHORIK, Yu.A.

Nature of inertial p-n junction diodes with small leakage rates
of the minority current carriers through a nonrectifying junction.
Radiotekh. i elektron. 10 no.6:1162-1163 Je '65.

(MIRA 18:6)

KLIMENKO, A.P. [Klymenko, A.P.; TKHORIK, Yu.A. [Tkhoryk, Iu.O.]

Use of the simultaneous diffusion of two admixtures in manufacturing quick-response diodes. Ukr. fiz. zhur. 10 no.2:238-239 F '65.

(MIRA 18:4)

1: Institut poluprovodnikov AN UkrSSR, Kiyev.

KLIMENKO, A.P. [Klymenko, A.P.]; TKHORIK, Yu.A. [Tkhoryk, IU.O.]

Effect of the duration of the pulse front on direct transients
in semiconductor diodes. Ukr. fiz. zhur. 9 no.11:1271-1273 N '64
(MIRA 18:1)

1. Institut poluprovodnikov AN UkrSSR, Kiyev.

GRIBNIKOV, Z.S. [Hrybnykov, Z.S.]; TKHORIK, Yu.A. [Tkhorik, Yu.A.]

Transient processes of storage and decay of nonequilibrium current carriers in semiconductor diodes. Part 1. Low injection levels. Ukr. fiz. zhur. 9 no.6:648-658 Je '64.
(MIRA 17:11)

1. Institut poluprovodnikov AN UkrSSR, Kiyev.

BONDARENKO, V.N.; LITVINOVA, E.M.; SNITKO, O.V.; TKHORIK, Yu.A.

Effect of thermal treatment and some coatings on the velocity
of Si and Ge surface recombination. Radiotekh. i elektron. 9
no. 5 876-881 My '64. (MIRA 17:7)

1. Institut poluprovodnikov AN UkrSSR.

ACCESSION NO. 1 APR 1986

AUTHOR: Tkhork, Yu. A.

TITLE: Effect of the recombination rate at the nonrectifying contact plane and the injection level upon the τ_{le} of $\text{p}-\text{Ge}$

SOURCE: Radiotekhnika i elektronika, 1985, v. 30, no. 10, p. 2300

TOPIC TAGS: semiconductor characteristics, depletion time, semiconductor property

ABSTRACT: Several Soviet and Western articles are briefly reviewed, figuring out the effect of the injection level on the recombination rate in $\text{p}-\text{Ge}$ diodes and $\text{p}-\text{Ge}$ of thick-base diodes. A formula for the recombination time is obtained.

Card 1/2

ACCESSION NR. APS-111

for his valuable hints, and T. M. Alexander for a discussion. Orig. art. has 3 figures and 10 formulas

ASSOCIATION none

SUBMITTED: 28Mar64

ENCL: 00

SUB CODE: EC

NO REF SOV: 006

OTHER: 005

Card 2/2 A.

Scanned by the Defense Technical Information Service
for the Defense Technical Information Center

ACCESSION NR: A94043324

1996-07-10 10:00:00 1996-07-10 10:00:00

AUTHOR: Klymenko, A. I. (Klymenko, A. I.), Tikhoryuk, Yu. O. (Tikhoryuk, Yu. A.)

TITLE: Investigation of recombination in nickel atoms in p-germanium
at high injection levels

SOURCE: Ukrayins'kyi fizychnyy zhurnal, v. 9, no. 7, 1964, 733-
743

TOPIC TAGS: injection level, current carrier recombination, current
carrier lifetime, diode saturation current, germanium, nickel, nickel
impurity concentration, semiconductor, semiconductor device, semicon-
ductor diode

ABSTRACT: The dependence of the lifetime τ of current carriers in p-
Ge diodes doped with Ni on the injection level and the temperature
has been investigated. It was found that in diodes the dependence of
 τ on temperature is weaker than in massive specimens because of the
influence of a surface recombination which efficiency increases with

Card 1/2

L 3827-65

ACCESSION NR: AP4043094

cooling. The theoretical and observed dependence of τ on the injection level agree qualitatively. The pulse method for measuring τ has been theoretically analyzed. The calculations show that the pulse method provides accurate values for τ_{a} and τ_{b} at vanishing small and superhigh injection levels. To reduce the errors in the region of medium injection levels, the parameter has to be increased for the measuring circuit I_2/I_1 , where I_1 is the amplitude of the forward current, and I_2 is the amplitude of the reverse current after switching off the diode. As an example, a calculation was made of the dependence of the injection level on the current density at the p-n junction in p-Ge with a concentration of $3 \times 10^{15} \text{ cm}^{-3}$ of Ni at 296K, 235K, and 185K. Orig. art. has: 6 figures and 44 formulas.

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KLIMENKO, A.P. [Klymenko, A.P.]; TKHORIK, Yu.A. [Tkhoryk, Yu.A.]

Study of recombinations on nickel atoms in p-germanium at high
injection levels. Ukr. fiz. zhur. 9 no.7:733-743 J1 '64.

(MIRA 17:10)

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TKHORIK, Yuriy Aleksandrovich [Tkhoryk, Iu.O.]; KISINA, I.V., red.izd-va;
RAKHLINA, N.P., tekhn.red.

[Semiconductors and electric power] Napivprovodnykova energetyka.
Kyiv, Vyd-vo Akad.nauk UkrSSR, 1959. 51 p. (MIRA 13:9)
(Semiconductors) (Photoelectric cells)

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TITLE: Concerning the problem of a transparent contact for II-VI
type photoconductors ~~21.44~~

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TOPIC TAGS: cadmium sulfide, cadmium compound, photoconductor,
photoconductivity, single crystal, optic property, electric property,
metal vapor deposition, volt ampere characteristic

ABSTRACT: The authors discuss the possibility of using CdO films as
transparent ohmic contacts for CdS-type photoconductors. The contact
properties of CdS single crystals and films with CdO films were in-
vestigated, along with the optical and electrical properties of CdO
films. The films were obtained by cathode sputtering of metallic

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cadmium in a low vacuum under the following conditions: cathode diameter -- 6 cm, cathode-anode distance -- 1.6 -- 1.8 cm, current -- 50 to 70 mA, voltage -- 600 V, air pressure -- 0.4 to 0.65 torr. Under these conditions the polycrystalline films were deposited at a rate of 500 -- 600 $\text{\AA}/\text{min}$. The resistivity of CdO films measured by the four-probe method amounted to $(3.2 -- 6.4) \times 10^{-3}$ ohm-cm, which does not contradict the data in the literature, and was temperature independent between -100 and 70C. The spectral dependence of the transmission coefficient was obtained. The volt-ampere characteristics of CdS films with CdO contacts were obtained at various temperature and illuminations. An investigation of the distribution of the potential along the CdS film with CdO contacts showed that the gradient of the potential decreases near the contacts. These results and also data on the noise characteristics of the contacts indicate that they are ohmic. Orig. art. has: 4 figures and 1 table.

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